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Amended
shown in the top view of Fig. 3f. Thus, a stacked-gate as shown in the cross-sectional view of Fig. 3g, is formed.

IN THE CLAIMS

Please amend claim 29 as follows:

Sub 1915
29. (AMENDED TWICE) A stacked-gate flash memory having a shallow trench isolation with a high-step oxide and high

3 lateral coupling comprising:

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a substrate having a gate oxide layer;

6
at least two trenches formed to a depth between about 2500 to 5000 Å below the surface of said substrate;

9
an oxide layer formed over said substrate, including over the inside walls of said two trenches;

12
a high-step oxide formed within said two trenches over said oxide liner and protruding upward over the surface of said
15 substrate to a height between about 2000 to 6000 Å;

said high-step oxide forming an opening with high walls

Sub
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over the surface of said substrate between said two
trenches;

13
21 a first conductive layer formed conformally inside said
opening and over the surface of the substrate between said
high walls to form a floating gate having folding surfaces;

24
an intergate oxide formed over said floating gate having
folding surfaces;

General
27
a second conductive layer formed protruding downward in
between said folding surfaces over said intergate oxide
30 layer to form a control gate; and

a self-aligned source (SAS) line.

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